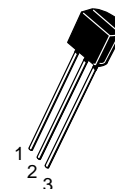
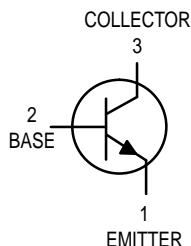


High Voltage Transistor

NPN Silicon

BF844



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	400	Vdc
Collector–Base Voltage	V_{CBO}	450	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	300	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	400	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 100 \mu\text{Adc}, V_{BE} = 0$)	$V_{(BR)CES}$	450	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	450	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 400 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	0.1	μAdc
Collector Cutoff Current ($V_{CE} = 400 \text{ Vdc}, V_{BE} = 0$)	I_{CES}	—	500	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	0.1	μAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ⁽¹⁾ ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 50\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	40 50 45 20	— 200 — —	—
Collector–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 1.0\text{ mAdc}$, $I_B = 0.1\text{ mAdc}$) ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$) ($I_C = 50\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)	$V_{CE(sat)}$	— — —	0.4 0.5 0.75	Vdc
Base–Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	$V_{BE(sat)}$	—	0.75	Vdc

DYNAMIC CHARACTERISTICS

High Frequency Current Gain ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 20\text{ MHz}$)	$ h_{fe} $	1.0	—	
Collector–Base Capacitance ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	—	6.0	pF
Emitter–Base Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ib}	—	110	pF
Turn–On Time ($V_{CC} = 150\text{ Vdc}$, $V_{BE(off)} = 4.0\text{ V}$, $I_C = 30\text{ mAdc}$, $I_{B1} = 3.0\text{ mAdc}$)	t_{on}	—	0.6	μs
Turn–Off Time ($V_{CC} = 150\text{ Vdc}$, $I_C = 30\text{ mAdc}$, $I_{B1} = I_{B2} = 3.0\text{ mAdc}$)	t_{off}	—	10	μs

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

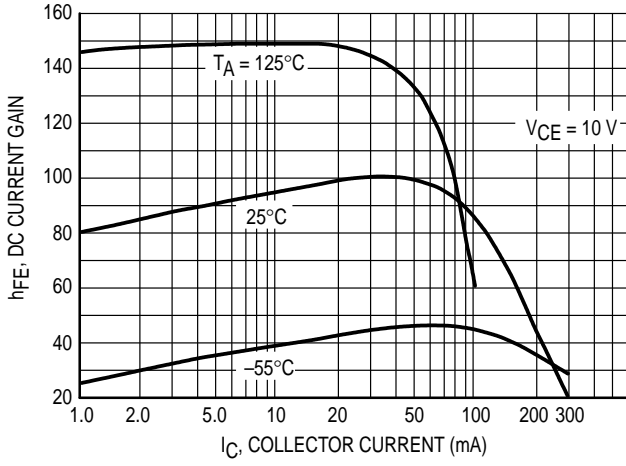


Figure 1. DC Current Gain

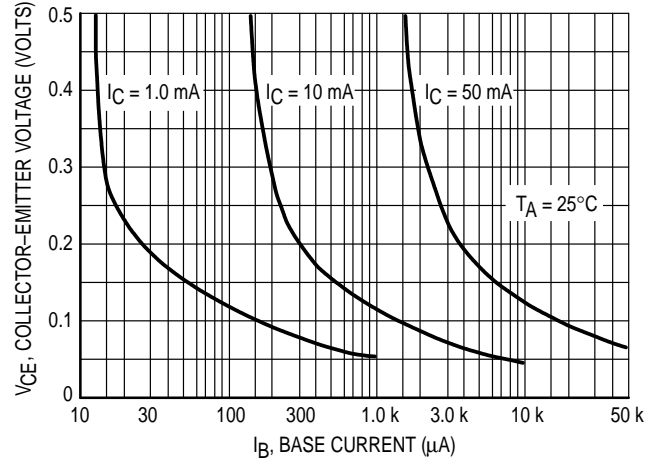


Figure 2. Collector Saturation Region

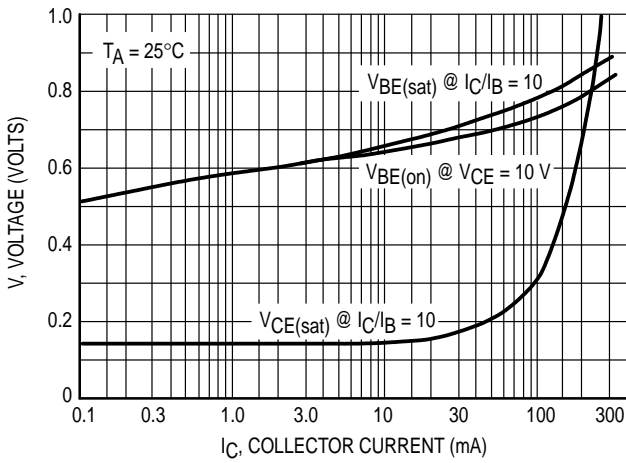


Figure 3. On Voltages

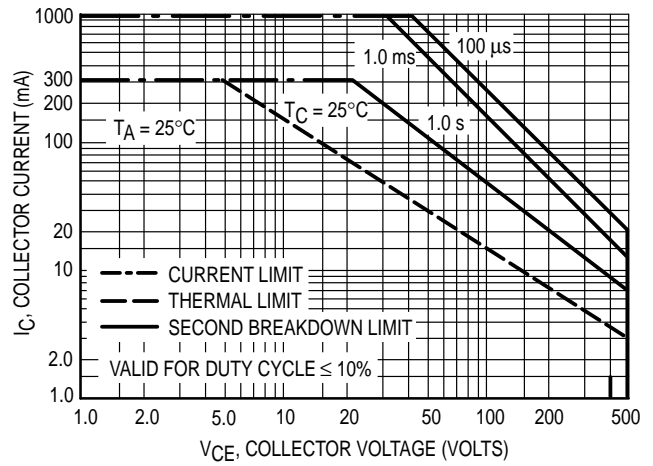


Figure 4. Active Region Safe Operating Area

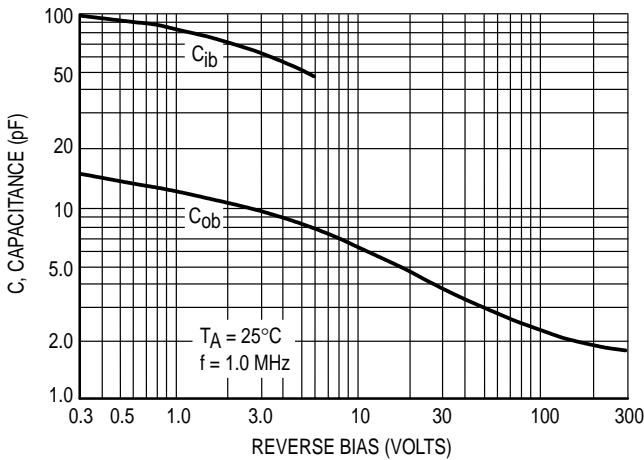


Figure 5. Capacitance

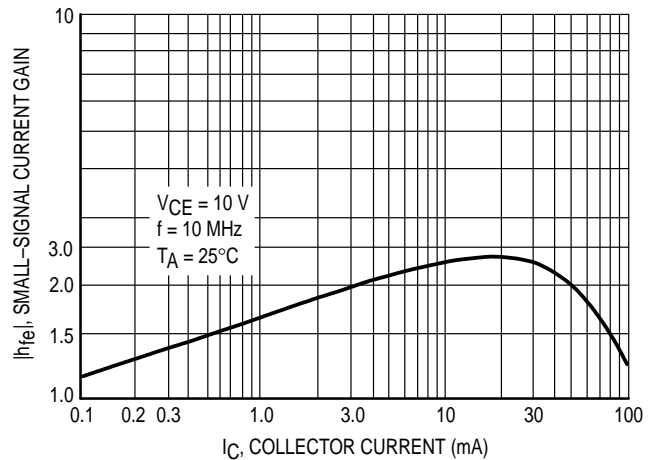


Figure 6. High Frequency Current Gain

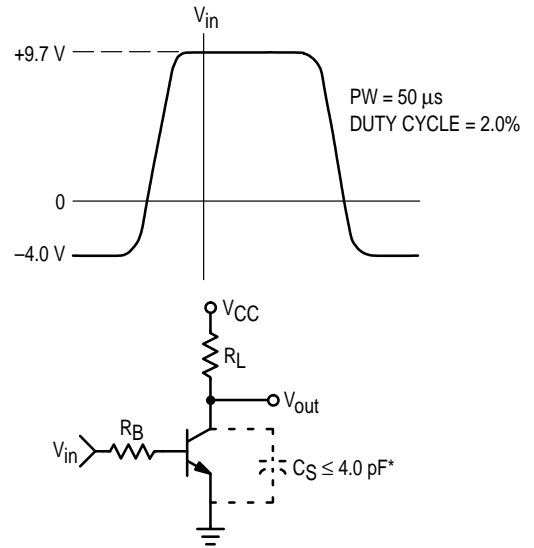
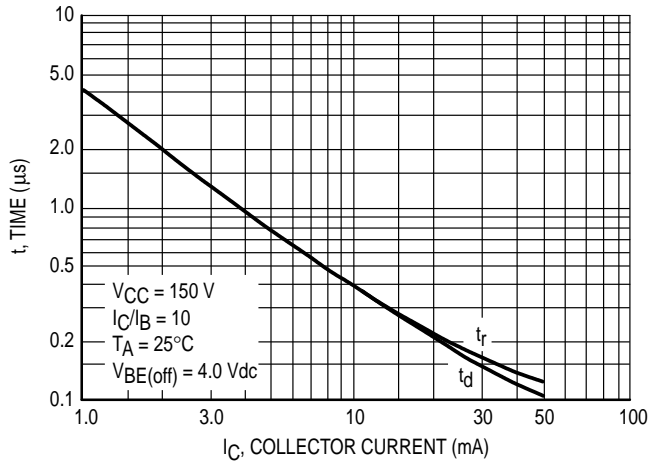


Figure 7. Turn-On Switching Times and Test Circuit

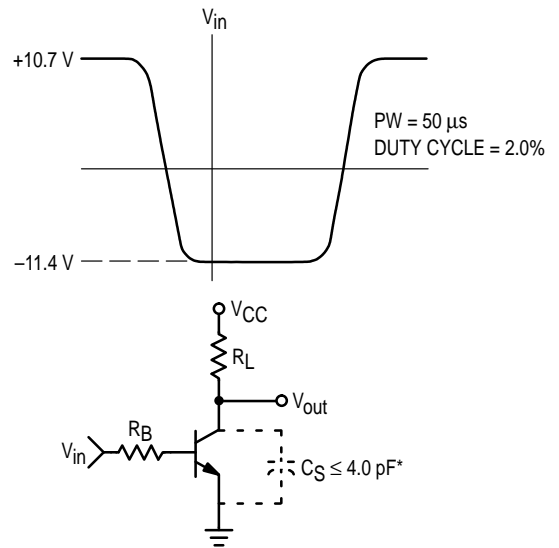
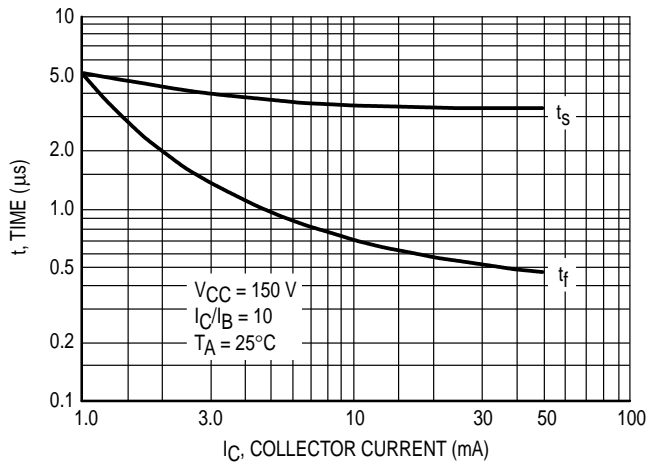
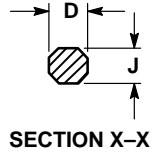
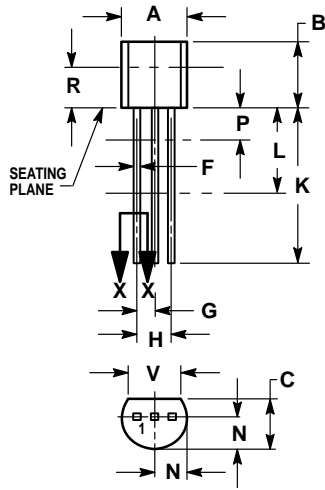


Figure 8. Turn-Off Switching Times and Test Circuit

* Total Shunt Capacitance of Test Jig and Connectors.

PACKAGE DIMENSIONS



CASE 029-04
(TO-226AA)
ISSUE AD


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K. MINIMUM LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 1:

- PIN 1. EMITTER
2. BASE
3. COLLECTOR

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